

NCE P-Channel Enhancement Mode Power MOSFET

Description

The NCE30P28Q uses advanced trench technology to provide excellent $R_{\text{DS(ON)}}$, This device is suitable for use as a load switch or power management.

Application

- Power management
- Load switch

General Features

• $V_{DS} = -30V, I_{D} = -28A$

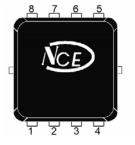
 $R_{DS(ON)}$ <9m Ω @ V_{GS} =-10V

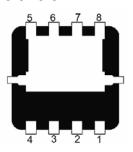
 $R_{DS(ON)}$ <17m Ω @ V_{GS} =-4.5V

- High power and current handing capability
- Lead free product is acquired
- Surface mount package

100% UIS TESTED! 100% ΔVds TESTED!

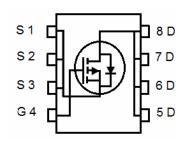
DFN 3.3X3.3





Top View

Bottom View



Schematic Diagram

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCE30P28Q	NCE30P28Q	DFN3.3X3.3-8L	Ø330mm	12mm	5000 units

Absolute Maximum Ratings (T_A=25 ℃unless otherwise noted)

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Parameter	Symbol	Limit	Unit			
Drain-Source Voltage	V _{DS}	-30	V			
Gate-Source Voltage	V _G s	±20	V			
Drain Current-Continuous	I _D	-28	Α			
Drain Current-Pulsed (Note 1)	I _{DM}	-80	Α			
Maximum Power Dissipation	P _D	40	W			
Operating Junction and Storage Temperature Range	T_{J}, T_{STG}	-55 To 150	$^{\circ}$ C			

Thermal Characteristic

Thermal Resistance, Junction-to-Case (Note 2)	R _{eJC}	3.13	°C/W
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Electrical Characteristics (T_A=25 °C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =-250μA	-30	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V_{DS} =-30 V , V_{GS} =0 V	-	-	-1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V,V _{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)	•				•	



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NCE30P28Q

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Gate Threshold Voltage	$V_{GS(th)}$	V _{DS} =V _{GS} ,I _D =-250μA	-1.0	-1.7	-2.5	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =-10V, I _D =-20A	-	6.7	9	mΩ
Diam-Source On-State Resistance	R _{DS(ON)}	V _{GS} =-4.5V, I _D =-20A	-	9.5	17	
Forward Transconductance	g FS	V _{DS} =-5V,I _D =-20A	-	25	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C _{lss}	\/ - 15\/\/ -0\/	-	2691.7	-	PF
Output Capacitance	C _{oss}	V_{DS} =-15V, V_{GS} =0V, F=1.0MHz	-	492.3	-	PF
Reverse Transfer Capacitance	C _{rss}	F=1.0WIFIZ	-	362.3	-	PF
Switching Characteristics (Note 4)	Switching Characteristics (Note 4)					
Turn-on Delay Time	t _{d(on)}		-	11	-	nS
Turn-on Rise Time	t _r	V _{DD} =-15V, ID=-20A,	-	9.4	-	nS
Turn-Off Delay Time	$t_{d(off)}$	V_{GS} =-10V, R_{GEN} =3 Ω	-	24	-	nS
Turn-Off Fall Time	t _f		-	12	-	nS
Total Gate Charge	Q_g		-	45.3	-	nC
Gate-Source Charge	Q_{gs}	V _{DS} =-15V,I _D =-20A,V _{GS} =-10V	-	6.1	-	nC
Gate-Drain Charge	Q_{gd}		-	13.5	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V,I _S =-28A	-	-	-1.2	V

Notes

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- 2. Surface Mounted on FR4 Board, t ≤ 10 sec.
- 3. Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2%.
- 4. Guaranteed by design, not subject to production



Typical Electrical and Thermal Characteristics

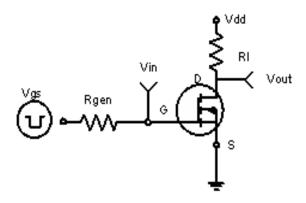


Figure 1 Switching Test Circuit

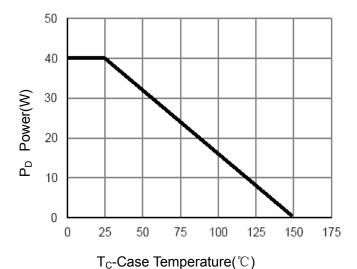


Figure 3 Power Dissipation

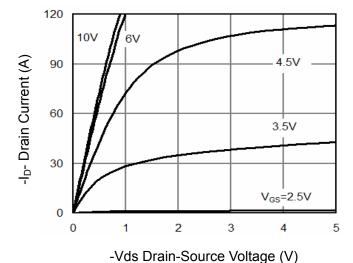


Figure 5 Output Characteristics

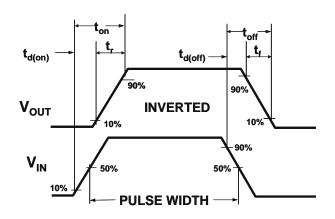


Figure 2 Switching Waveforms

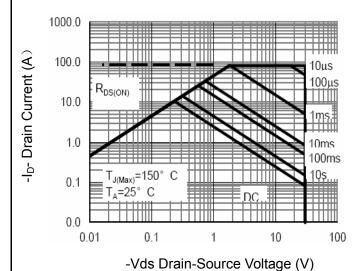


Figure 4 Safe Operation Area

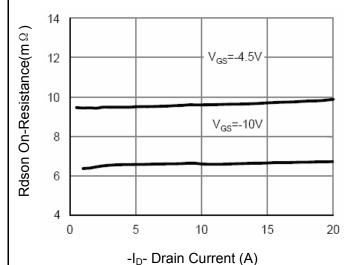


Figure 6 Drain-Source On-Resistance



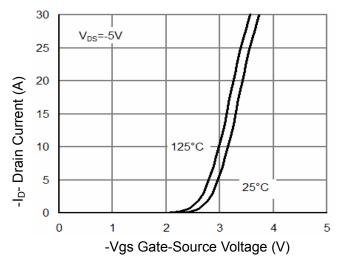
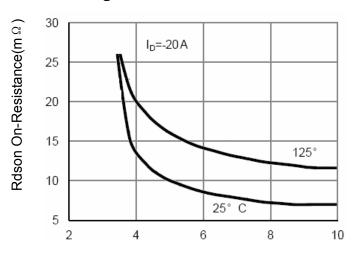


Figure 7 Transfer Characteristics



-Vgs Gate-Source Voltage (V)
Figure 9 Rdson vs Vgs

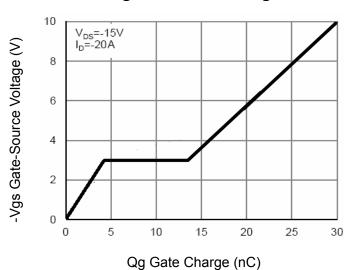
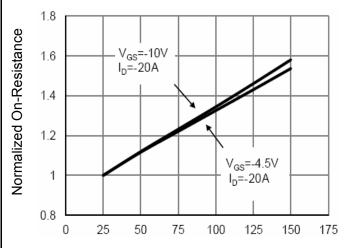
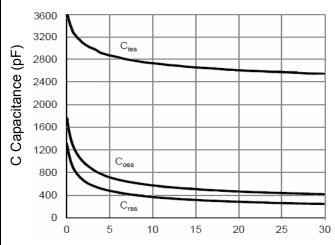


Figure 11 Gate Charge



T_J-Junction Temperature(°C)





-Vds Drain-Source Voltage (V)

Figure 10 Capacitance vs Vds

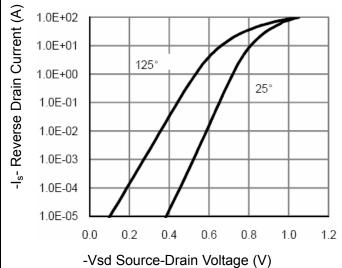


Figure 12 Source- Drain Diode Forward



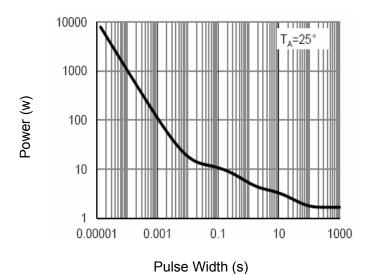


Figure 13 Single Pulse Power Rating Junction-to Ambient (Note 6)

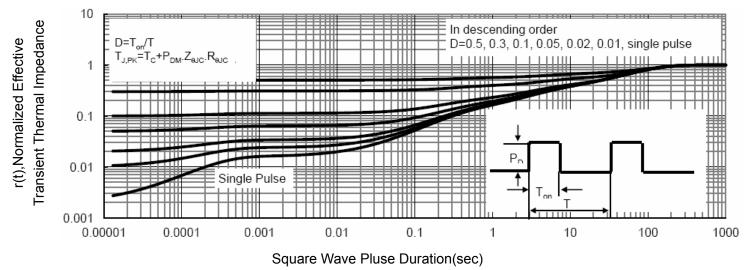
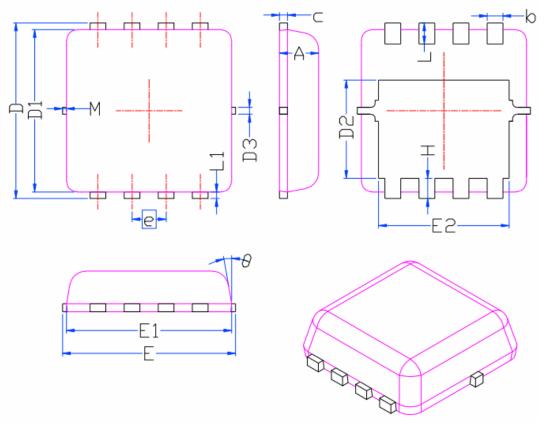


Figure 14 Normalized Maximum Transient Thermal Impedance

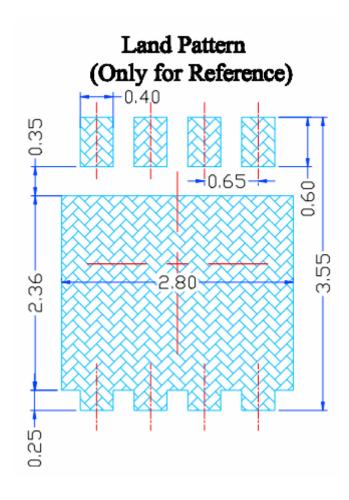


DFN3.3X3.3-8L Package Information



Cumbal	Dimensions In Millimeters					
Symbol	Min.	Nom.	Max.			
A	0.70	0.75	0.80			
b	0.25	0.30	0.35			
С	0.10	0.15	0.25			
D	3.25	3.35	3.45			
D1	3.00	3.10	3.20			
D2	1.78	1.88	1.98			
D3	-	0.13	-			
E	3.10	3.20	3.30			
E1	3.00	3.15	3.20			
E2	2.39	2.49	2.59			
е	0.65BSC					
Н	0.30	0.39	0.50			
L	0.30	0.40	0.50			
L1	-	0.13	-			
М	*	*	0.15			
θ		10°	12 [°]			







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